G. Device & Process Modeling, Simulation and Reliability 분과

2017년 2월 14일 (화), 08:30-10:00
Room C (사파이어, 2층)

[TC1-G] Device Physics and Characterization 1

좌장: 김대환(국민대학교), 조인욱(SK 하이닉스)

TC1-G-1 **08:30-08:45**	**DFT Study on the Clean-Up Mechanism of InGaAs(001) Native Oxides in Atomic Layer Deposition** In Won Yeu[1,2], Cheol Seong Hwang[2,3], and Jung-Hae Choi[1] *[1]Center for Electronic Materials, Korea Institute of Science and Technology, [2]Department of Materials Science and Engineering, Seoul National University, [3]Inter-University Semiconductor Research Center, Seoul National University*
TC1-G-2 **08:45-09:00**	**Analysis of Hysteresis Characteristic in 3-D NAND Flash Memory Cells** Ho-Jung Kang, Nagyong Choi, Byung-Gook Park, and Jong-Ho Lee *Department of EECS and ISRC, Seoul National University*
TC1-G-3 **09:00-09:15**	**Charge Transport Mechanism and Low-Frequency Noise Properties in High Mobility ZnON Thin-Film Transistors** Chan-Yong Jeong[1], Hee-Joong Kim[1], Dae-Hwan Kim[1], Hyun-Suk Kim[2], Eok Su Kim[3], Tae Sang Kim[3], Joon Seok Park[3], Jong-Baek Seon[3], Kyoung Seok Son[3], Sunhee Lee[3], Seong-Ho Cho[3], Young Soo Park[3], Dae Hwan Kim[4], and Hyuck-In Kwon[1] *[1]School of Electrical and Electronics Engineering, Chung-Ang University, [2]Department of Material Science and Engineering, Chungnam National University, [3]Samsung Advanced Institute of Technology, [4]School of Electrical Engineering, Kookmin University*
TC1-G-4 **09:15-09:30**	**HfO2(Field Effect Passivation Layer)를 적용한 CMOS image sensor의 Dark current 특성 연구** Seon Man Hwang and Yong Hoon Choi *SK Hynix Inc.*
TC1-G-5 **09:30-09:45**	**A Trap Characterization Method for Float Body PMOSFET Using Pulsed Drain Current Transient** Manh-Cuong Nguyen, Hack-Yeon Kim, Jae-Won Choi, Soo-Yeun Han, An Hoang-Thuy Nguyen, Jungyeon Kim, Sang-Woo Kim, Su-Jin Choi, Jong-Kyu Jun, and Rino Choi *Department of Materials Science and Engineering, Inha University*
TC1-G-6 **09:45-10:00**	**Influence of Active Layer Thickness on the Abnormal Output Characteristics in Amorphous In-Ga-Zn-O TFTs under High Current-Flowing Operation** Hye Ri Yu, Jun Tae Jang, Sungju Choi, Hara Kang, Daehyun Ko, Jaeyoung Kim, Geumho Ahn, Jihyun Lee, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim *School of Electrical Engineering, Kookmin University*